

Form 1449*	Atty. Docket No.: 303.379US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Wendell P. Noble et al.	09/551027
	Filing Date: Herewith	Group: Unknown

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
M.T.	3,806,741	04/23/1974	Smith	307	304	05/17/72
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	4,604,162	08/05/1986	Sobczak, Z.P.	156	657	12/23/85
	4,663,831	05/12/1987	Birrittella, M.S., et al.	29	576 E	10/08/85
	4,673,962	06/16/1987	Chatterjee, P.K., et al.	357	23.6	03/21/85
	4,761,768	08/02/1988	Turner, J.E., et al.	365	201	03/04/85
	4,766,569	08/23/1988	Turner, J.E., et al.	365	185	06/05/86
	4,920,065	04/24/1990	Chin, D., et al.	437	52	10/27/89
	4,958,318	09/18/1990	Harari, E.	365	149	07/08/88
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	5,177,028	01/05/1993	Manning	437	41	10/22/91
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	5,202,278	04/13/1993	Mathews, et al.	437	47	09/10/91
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M.T.	5,396,093	03/07/1995	Lu	257	306	08/12/94

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	5,414,287	05/09/1995	Hong, G.	257	316	04/25/94
	5,422,499	06/06/1995	Manning, M.	257	67	02/22/93
	5,427,972	06/27/1995	Shimizu, M., et al.	437	52	04/18/90
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M.T.	363066963A	03/01/1988	Japan	257	305	X

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